

٢٠٠ / Descriptions

SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

• ٤ / Features

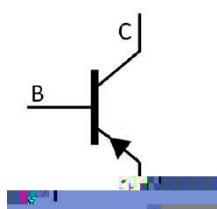
2SD1898

High breakdown voltage, good h_{FE} linearity, low $V_{CE(sat)}$, complements the 2SD1898.

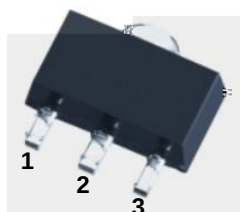
٧ ٥ / Applications

General power amplifier applications.

٧ ٥ ٤ = ٤ / Equivalent Circuit



٤ ١ ٥ / Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

٤. ٨ ٥ / Marking

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82` 180	120` 270	180` 390
Marking	HBHP*	HBHQ*	HBHR*

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.0	A
Collector Current-Continuous(Pulse)	$*I_{CP}$	-2.0	A
Collector Power Dissipation	$**P_C$	0.5	W
	$*P_C$	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55° 150	

*Single pulse $P_w=100ms$

100ms $\hat{A}$

**mounted on 40×40×0.7mm ceramic board

40×40×0.7m

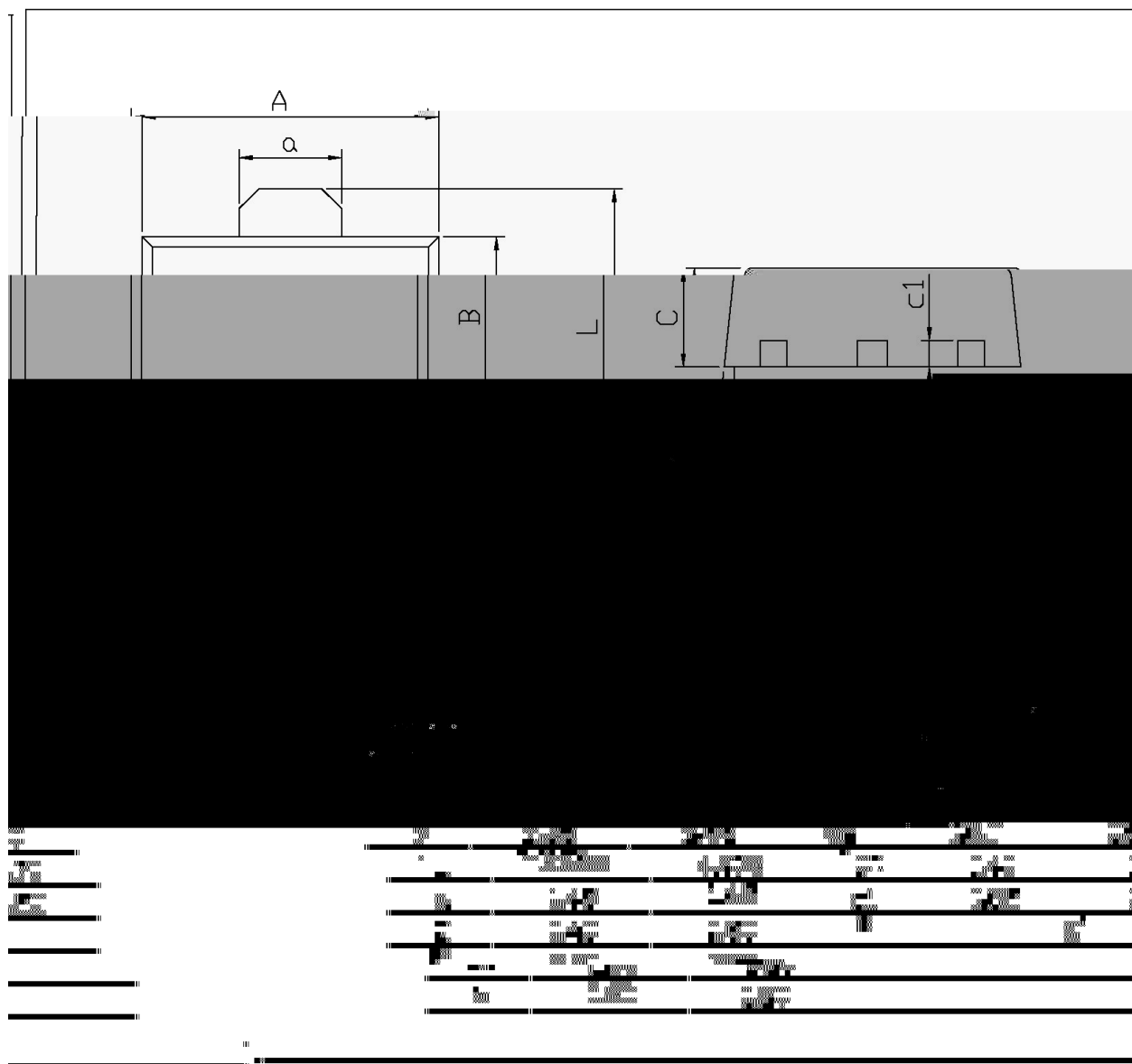
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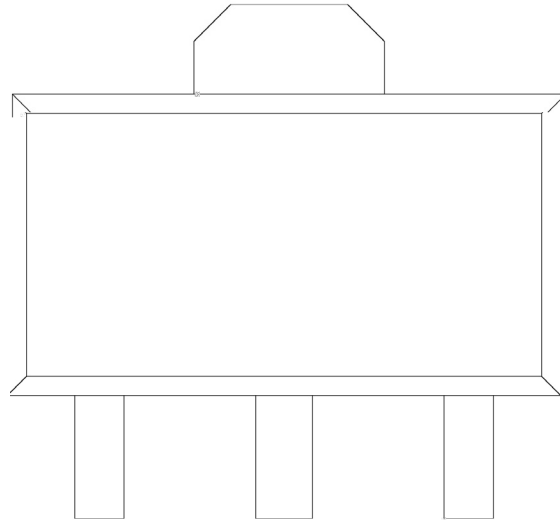
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C				

⊂ É Ò L f / Package Dimensions

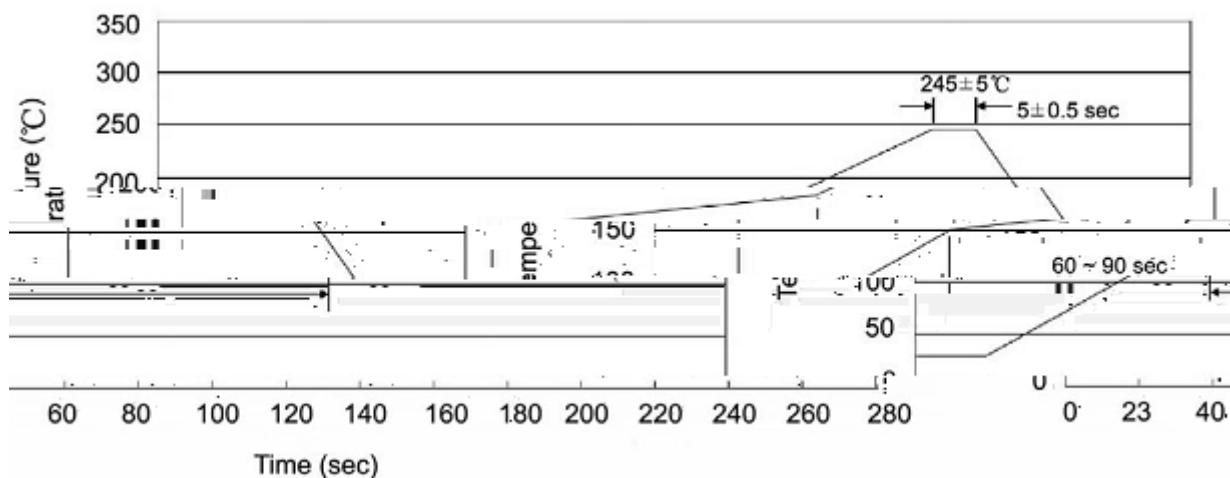
STT-89

单位: mm





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Note:

1. Preheating: 25~150 , Time: 60~90sec.
2. Peak Temp.: 245±5 , Duration: 5±0.5sec.
3. Cooling Speed: 2~10 /sec.

Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.: 260±5 Time: 10±1 sec

Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-89	1,000	7	7,000	8	56,000	7 ρ ×12		